FAIRCHILD

SEMICONDUCTOR ™

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NDH832P
## P-Channel Enhancement Mode Field Effect Transistor

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General Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- -4.2A, -20V. $R_{DS(ON)} = 0.06\Omega$ @ $V_{GS} = -4.5V$
  $R_{DS(ON)} = 0.08\Omega$ @ $V_{GS} = -2.7V$.
- High density cell design for extremely low $R_{DS(ON)}$.
- Enhanced SuperSOT™-8 small outline surface mount package with high power and current handling capability.

SuperSOT™-8
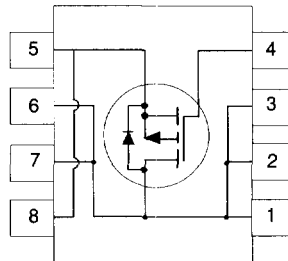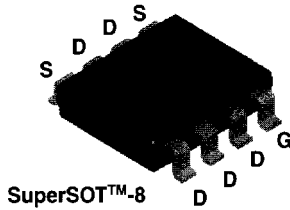
Absolute Maximum Ratings $T_A = 25°C$ unless otherwise noted

Symbol	Parameter		NDH832P	Units
V_{DSS}	Drain-Source Voltage		-20	V
V_{GSS}	Gate-Source Voltage		-8	V
I_D	Drain Current - Continuous	(Note 1a)	-4.2	A
	- Pulsed		-15	
P_D	Maximum Power Dissipation	(Note 1a)	1.8	W
		(Note 1b)	1	
		(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to 150	°C
THERMAL CHARACTERISTICS				
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	70	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	20	°C/W

Electrical Characteristics ($T_A = 25°C$ unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
OFF CHARACTERISTICS							
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0$ V, $I_D = -250$ μA		-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16$ V, $V_{GS} = 0$ V				-1	μA
			$T_J = 55°C$			-10	μA
I_{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 8$ V, $V_{DS} = 0$ V				100	nA
I_{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -8$ V, $V_{DS} = 0$ V				-100	nA
ON CHARACTERISTICS (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250$ μA		-0.4	-0.7	-1	V
			$T_J = 125°C$	-0.3	-0.5	-0.8	
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5$ V, $I_D = -4.2$ A			0.045	0.06	Ω
			$T_J = 125°C$		0.063	0.12	
		$V_{GS} = -2.7$ V, $I_D = -3.7$ A			0.064	0.08	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5$ V, $V_{DS} = -5$ V		-15			A
		$V_{GS} = -2.7$ V, $V_{DS} = -5$ V		-5			
g_{FS}	Forward Transconductance	$V_{DS} = -10$ V, $I_D = -4.2$ A			9		S
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	$V_{DS} = -10$ V, $V_{GS} = 0$ V, f = 1.0 MHz			1000		pF
C_{oss}	Output Capacitance				530		pF
C_{rss}	Reverse Transfer Capacitance				180		pF
SWITCHING CHARACTERISTICS (Note 2)							
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = -5$ V, $I_D = -1$ A, $V_{GEN} = -4.5$ V, $R_{GEN} = 6$ Ω			13	20	ns
t_r	Turn - On Rise Time				53	70	ns
$t_{D(off)}$	Turn - Off Delay Time				60	80	ns
t_f	Turn - Off Fall Time				33	40	ns
Q_g	Total Gate Charge	$V_{DS} = -10$ V, $I_D = -4.2$ A, $V_{GS} = -4.5$ V			18	30	nC
Q_{gs}	Gate-Source Charge				1.2		nC
Q_{gd}	Gate-Drain Charge				6		nC

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Electrical Characteristics (T$_A$ = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I$_S$	Maximum Continuous Drain-Source Diode Forward Current				-1.5	A
V$_{SD}$	Drain-Source Diode Forward Voltage	V$_{GS}$ = 0 V, I$_S$ = -1.5 A (Note 2)		-0.75	-1.2	V

Notes:

1. R$_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R$_{\theta JC}$ is guaranteed by design while R$_{\theta CA}$ is determined by the user's board design.

$$P_D(t) = \frac{T_J - T_A}{R_{\theta JA}(t)} = \frac{T_J - T_A}{R_{\theta JC} + R_{\theta CA}(t)} = I_D^2(t) \times R_{DS(ON)@T_J}$$

Typical R$_{\theta JA}$ using the board layouts shown below on 4.5"x5" FR-4 PCB in a still air environment:

    a. 70°C/W when mounted on a 1 in² pad of 2oz copper.

    b. 125°C/W when mounted on a 0.026 in² pad of 2oz copper.

    c. 135°C/W when mounted on a 0.005 in² pad of 2oz copper.

1a

1b

1c
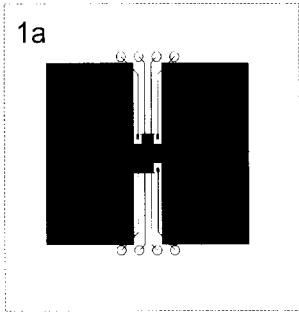
Scale 1 : 1 on letter size paper
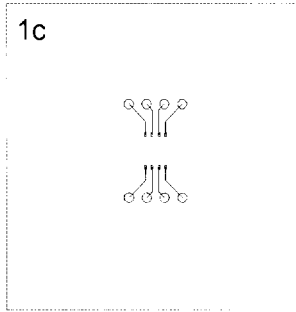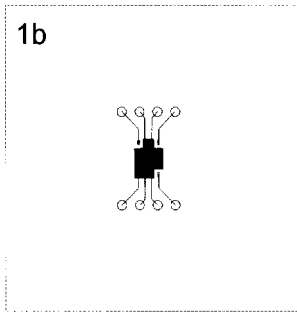
2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

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Typical Electrical Characteristics
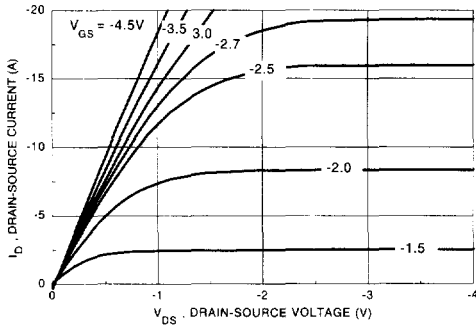
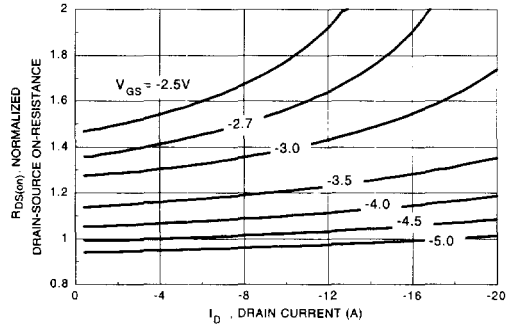**Figure 1. On-Region Characteristics.**

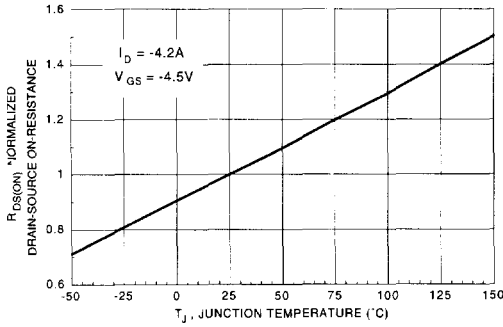**Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.**

Figure 3. On-Resistance Variation with Temperature.
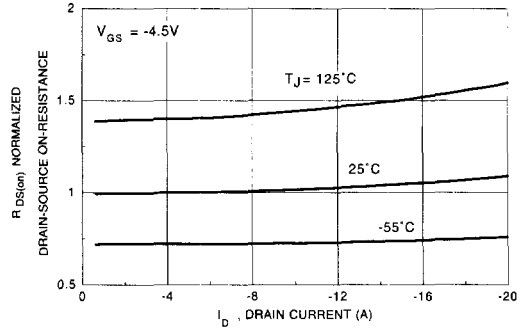

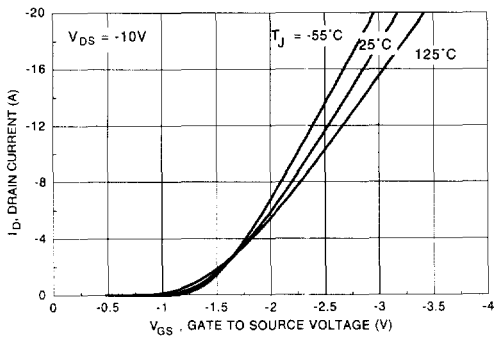**Figure 4. On-Resistance Variation with Drain Current and Temperature.**
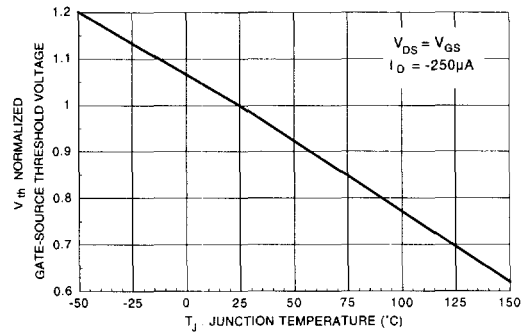

Figure 5. Transfer Characteristics.

Figure 6. Gate Threshold Variation with Temperature.
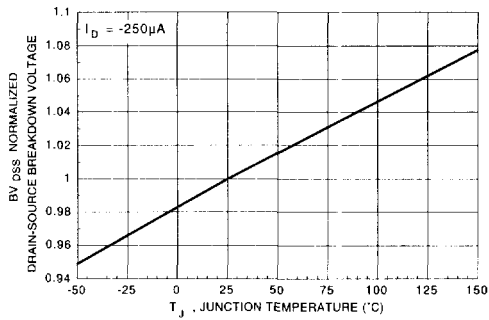
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Typical Electrical Characteristics

Figure 7. Breakdown Voltage Variation with Temperature.
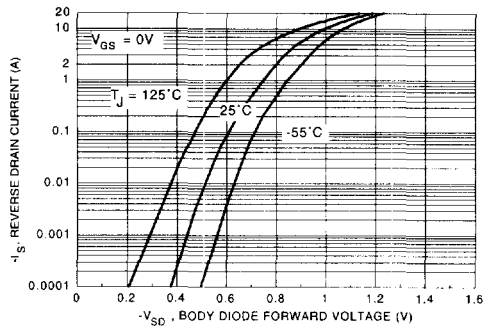
Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

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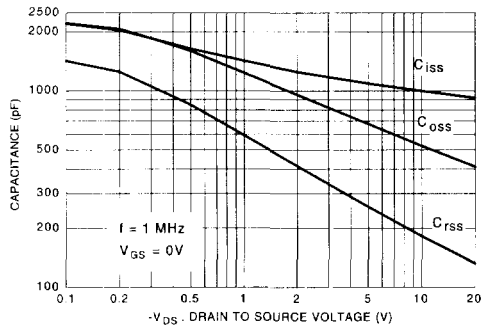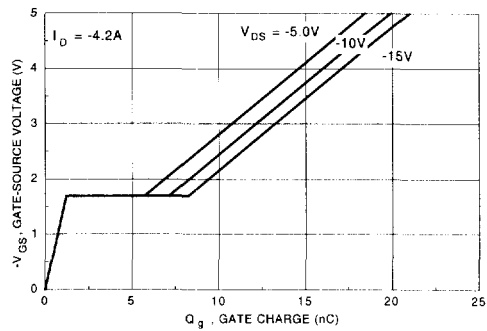

Figure 9. Capacitance Characteristics.
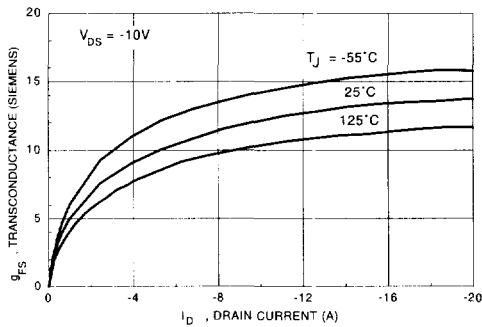

Figure 10. Gate Charge Characteristics.

Figure 11. Transconductance Variation with Drain Current and Temperature.

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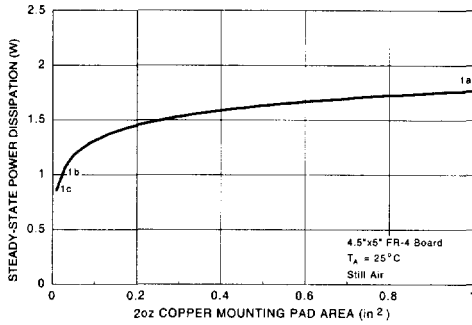## Typical Thermal Characteristics

Figure 12. SOT-8 Maximum Steady-State Power Dissipation versus Copper Mounting Pad Area.
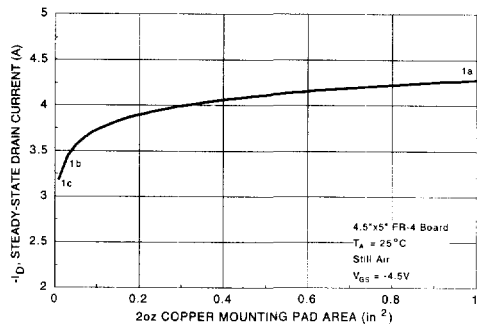

Figure 13. Maximum Steady-State Drain Current versus Copper Mounting Pad Area.
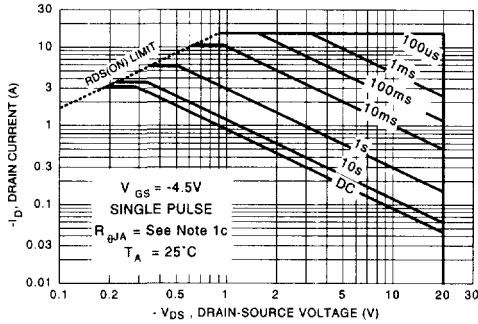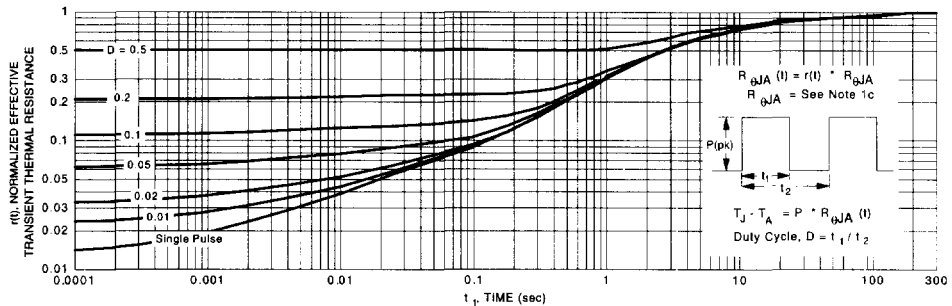

Figure 14. Maximum Safe Operating Area.

Figure 15. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.